

ABSTRACT

PLASMA-ENHANCED ETCHING IN AN AUGMENTED PLASMA PROCESSING SYSTEM.

Methods for etching a substrate in a plasma processing chamber having at least a primary plasma generating region and a secondary plasma generating region separated from said primary plasma generating region by a semi-barrier structure. The method includes generating a primary plasma from a primary feed gas in the primary plasma generating region. The method also includes generating a secondary plasma from a secondary feed gas in the secondary plasma generating region to enable at least some species from the secondary plasma to migrate into the primary plasma generating region. The method additionally includes etching the substrate with the primary plasma after the primary plasma has been augmented with migrated species from the secondary plasma.

FIG. 1



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